

wherein the first semiconductor substrate and the second semiconductor substrate are brought together so that the concave-convex surface of the first semiconductor substrate and the thin film insulator provided on the surface of the second semiconductor substrate contact each other with no circuit or device element located therebetween, to form a cavity in the semiconductor substrate device.

6. (Amended) A semiconductor substrate device, comprising:

a first semiconductor substrate including a concave-convex surface; and

a second semiconductor substrate having a thin film oxide insulator on a surface thereof, the surface of the second semiconductor substrate on which the thin film oxide insulator is provided being implanted with hydrogen ions,

wherein the first semiconductor substrate and the second semiconductor substrate are brought together so that the concave-convex surface of the first semiconductor substrate and the thin film oxide insulator provided on the ion implanted surface of the second semiconductor substrate contact each other with no circuit or device element located therebetween, to form a cavity in the semiconductor substrate device.

7. (Amended) A semiconductor substrate device, comprising:

a first semiconductor substrate including a concave-convex surface;

a second semiconductor substrate having a thin film Si layer on a surface thereof,

wherein the first semiconductor substrate and the second semiconductor substrate

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insulator

are brought together so that the concave-convex surface of the first semiconductor substrate and the thin film Si layer provided on the second semiconductor substrate contact each other with no circuit or device element located therebetween, to form a cavity in the semiconductor substrate device.

Please add the following new claims:

12. (New) The device of claim 1, wherein the non-glass thin film insulator has a thickness less than a thickness of the second semiconductor substrate on which the thin film insulator is provided, and wherein the thin film insulator is not a semiconductor.

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13. (New) The device of claim 7, wherein the thin film Si layer has a thickness less than a thickness of the second semiconductor substrate on which the thin film Si layer is provided.

REMARKS

This is in response to the Office Action dated September 30, 2002. New claims 12-13 have been added. Thus, claims 1, 2 and 6-13 are pending. Attached hereto is a marked-up version of the changes made to the claim(s) by the current amendment. The attached page(s) is captioned "Version With Markings To Show Changes Made."